

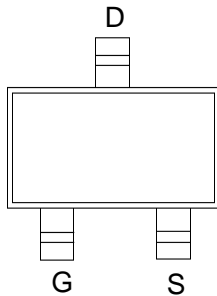
30V/2.2A N-Channel MOSFET

Features

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching

Application

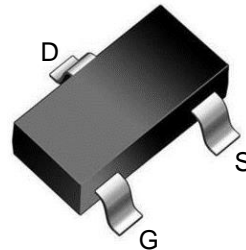
- Battery protection
- Load switch
- Power management



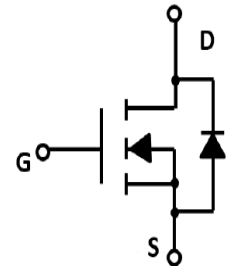
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	65m Ω @4.5V	2.2A
	82m Ω @2.5V	



SOT-23 top view



Schematic diagram

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		30	V
V_{GS}	Gate-Source Voltage		± 8	V
T_J	Maximum Junction Temperature		150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range		-50 to 155	$^{\circ}\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}\text{C}$	2.2	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}\text{C}$	10	A
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	2.2	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	0.5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		250	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	VDS=24V, VGS=0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	VGS=±8V, VDS=0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS, ID=250μA	0.6	0.9	1.2	V
R _{DS(on)}	Drain-Source On-State Resistance	VGS=4.5V, ID=2.2A	--	40	65	mΩ
		VGS=2.5V, ID=2.0A	--	55	82	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	VDS=15V, VGS=0V, f=1MHz	--	285	--	pF
C _{OSS}	Output Capacitance		--	33	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	27	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	VDS=15V, ID=4A, VGS=4.5V	--	2.6	--	nC
Q _{gs}	Gate Source Charge		--	0.6	--	nC
Q _{gd}	Gate Drain Charge		--	0.9	--	nC
t _{d(on)}	Turn-on Delay Time	VDD=15V, ID=2A, VGS=4.5V, RG=3Ω	--	15	--	nS
t _r	Turn-on Rise Time		--	42	--	nS
t _{d(off)}	Turn-Off Delay Time		--	16	--	nS
t _f	Turn-Off Fall Time		--	10	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =2.2A,	--	--	1.2	V

Typical Operating Characteristics

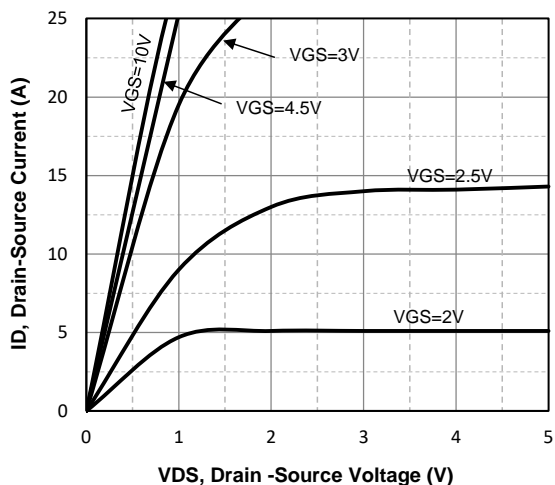


Fig1. Typical Output Characteristics

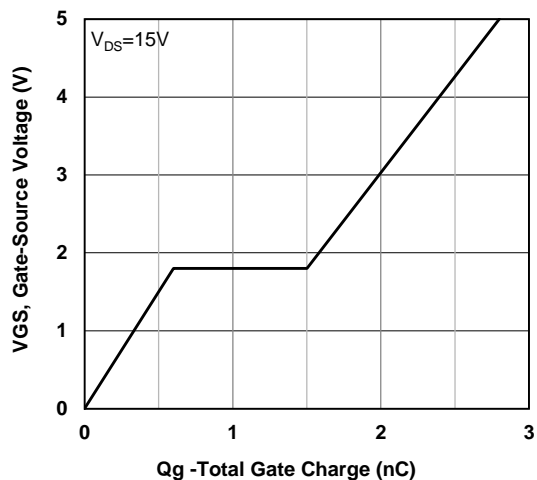


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

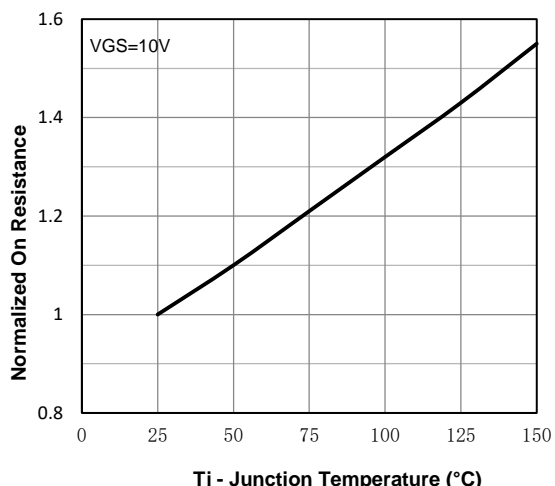


Fig3. Normalized On-Resistance Vs. Temperature

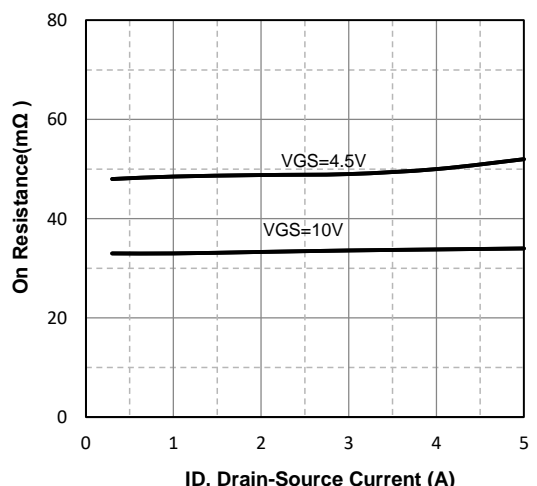


Fig4. On-Resistance Vs. Drain-Source

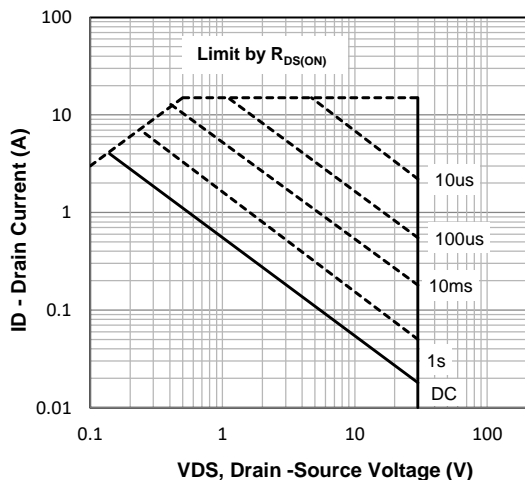


Fig5. Maximum Safe Operating Area

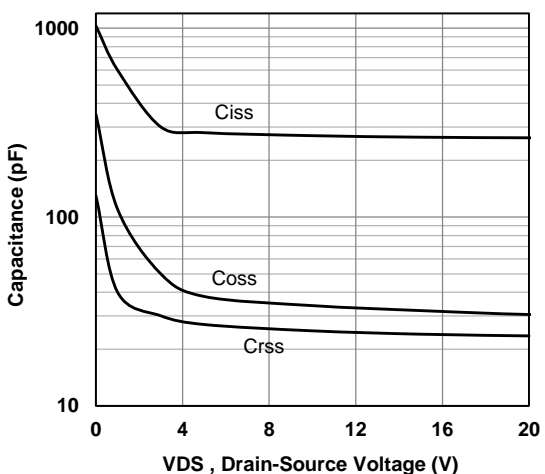
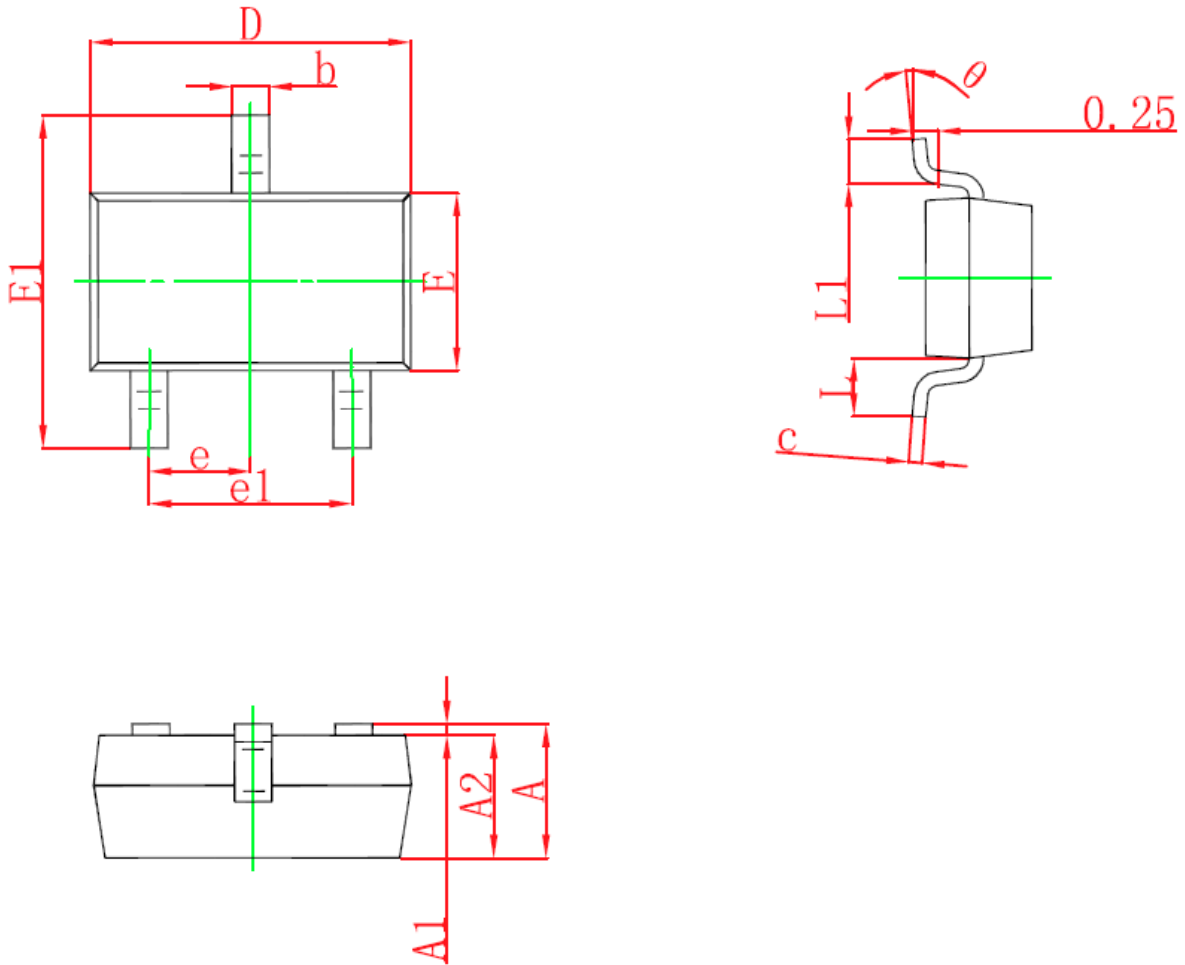


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°